



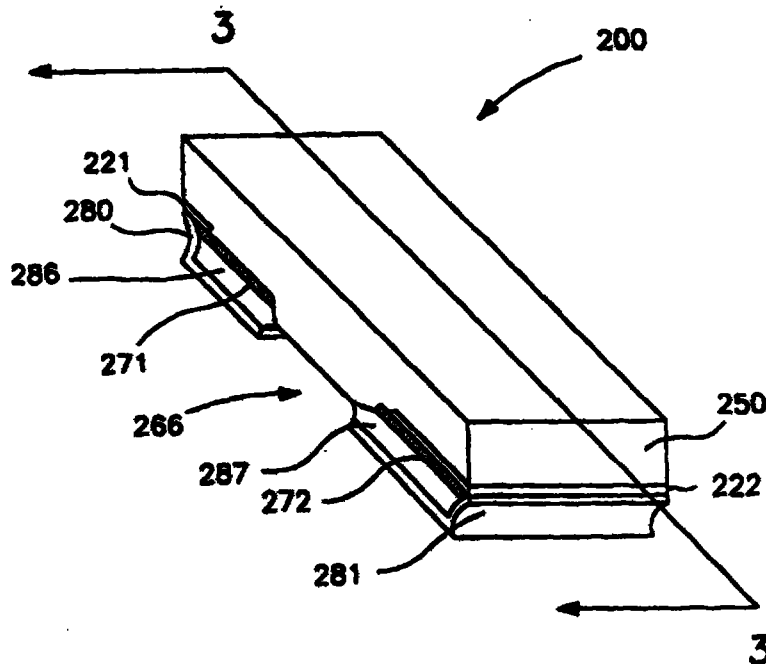
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(54) Title: **SEMICONDUCTOR FABRICATION WITH CONTACT PROCESSING FOR WRAP-AROUND FLANGE INTERFACE**

(57) Abstract

A flange interface for wrap-around contact regions formed in fabricating semiconductor devices provides for a durable and reliable electrical bond. A first layer having a first material is formed over the first side of a wafer. A trench is formed from the second side of the wafer such that a portion of the first layer becomes exposed in the trench. A second layer having a second material is formed over the second side of the wafer such that a portion of the second layer contacts the portion of the first layer exposed in the trench. The wafer is separated through the trench. The trench may be formed by sawing the second side of the wafer in an area where the trench is to be formed. The wafer may then be etched such that the trench is formed.



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